

Single-electron heat diode

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We introduce a new functional nanoscale device, a single-electron heat diode, consisting of two quantum dots or metallic islands coupled to electronic reservoirs by tunnel contacts. Electron transport through the system is forbidden but the capacitive coupling between the two dots allows electronic fluctuations to transmit heat between the reservoirs. When the reservoir temperatures are biased in the forward direction, heat flow is enabled by a four-step sequential tunneling cycle, while in the reverse-biased configuration this process is suppressed due to Coulomb blockade effects. In an optimal setup the leakage heat current in the reverse direction is only a few percent of the forward current.

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Understanding the thermal transport properties of nanoscale systems offers insight into fundamental physics as well as opens up possibilities for new applications. In a solid-state environment heat is generally carried by phonons and electrons, the latter offering much more flexibility in manipulation and measurement. Therefore in recent years there has been a great deal of interest to study heat control with mesoscopic electronics, including devices for cooling,¹ thermoelectric power generation,^{2,3} and thermal rectification.⁴ These advances suggest that in the near future thermal currents could be manipulated with a similar level of versatility as electrons today. This entails the construction of complicated heattronic circuits out of elementary components. One basic building block in electronics is a diode, and its heattronic counterpart, a heat diode, is a two-terminal device that allows energy to flow only in one direction. More precisely, with a temperature bias in the forward direction, a heat current J_+ flows between the terminals, while reversing the temperatures makes the current drop to J_- . For a proper diode operation these two values should be separated by at least an order of magnitude, that is, the rectification ratio J_+/J_- should be at least of the order of 10. In this Rapid Communication we introduce a new heat diode design where this requirement is easily fulfilled. That should be compared to recent experimental demonstrations of asymmetric heat flow⁴⁻⁶ where the ratio has been much below 2. We also emphasize that although there is a considerable body of theoretical literature on thermal rectification (see, for example, Ref. 7 and references therein), it is mostly concerned with simple model systems with no concrete realizations available, while the present proposal can be straightforwardly fabricated and operated with current experimental technology.

Our proposed device is a single-electron heat diode, consisting of two semiconductor quantum dots or two metallic islands (collectively called *dots*), coupled to different reservoirs (L and R) through tunnel barriers (Fig. 1). The coupling between the dots is purely capacitive so that there is no electron transport through the system. However, with a temperature difference be-

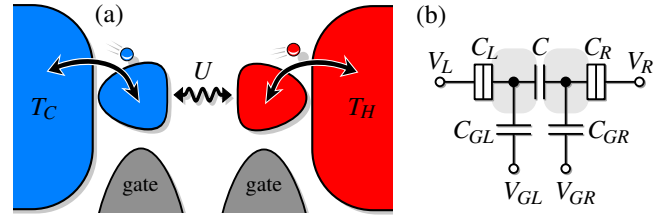


FIG. 1. (color online). (a) Schematic of the heat diode, shown here with a forward bias. Electrons hop in and out of the dots and exchange heat through Coulomb interaction U . (b) Circuit diagram for the diode with capacitances and external voltages indicated. Shaded areas correspond to the dots.

tween the reservoirs, thermal current is generated by electrons tunneling in and out of the dots and exchanging energy through Coulomb interaction. This energy transport mechanism has been previously studied in Ref. 3 in the context of a mesoscopic heat engine. Here we extend the idea to produce a rectifying mechanism for heat currents. Let us fix the notation by stipulating that in the forward direction the right reservoir is hot and the left one is cold, with temperatures T_H and T_C , respectively. The energy required for an electron to tunnel from reservoir α into the adjoining dot is $E_{\alpha n}$, where n is the occupation of the other dot. With two gate voltages the level structure of the double dot can be tuned to such a regime where the occupation of each dot may only be 0 or 1, and where the energies E_{Ln} are of the same order as T_C and the energies E_{Rn} are much larger, at least as large as T_H (Fig. 2). Now one quantum of heat, equal to the Coulomb interaction energy $U = E_{L1} - E_{L0} = E_{R1} - E_{R0}$, can be transported from right to left with the four-step cycle depicted on the left side of Fig. 2(b). The time-reversed cycle carries heat in the other direction, and the total current is the sum of these two contributions. When the temperatures are reversed, electrons from the right reservoir, now at the low temperature T_C , are unable to tunnel into the adjoining dot because the available thermal energy is much smaller than the required energies E_{Rn} . Therefore the heat-carrying cycle is exponentially

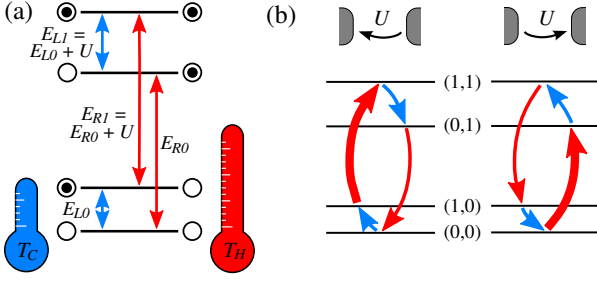


FIG. 2. (color online). (a) Energy-level diagram of the double-dot system. (b) Sequential tunneling cycles transporting a heat quantum U between the reservoirs. The processes denoted by the thick arrows become suppressed under reverse bias.

suppressed and heat flow is blocked. This asymmetric Coulomb blockade configuration is the origin of the diode effect. The general idea of producing rectification by coupling the left and right reservoirs to different transitions of the central system has been previously discussed in Ref. 8.

The rest of the paper is organized as follows. First we present the device model in detail and calculate the heat current in the sequential tunneling approximation. Then we show quantitatively how the diode effect arises in the proposed device, considering two realizations, metallic islands with a continuous spectrum and quantum dots with discrete states, and conclude that their behavior is essentially identical. We analyze the conditions for optimal diode operation and show how to obtain the required level structure with a double-dot setup. Finally we consider the experimental demonstration of the diode effect.

The system is modeled with

$$H = \sum_{\alpha=L,R} (H_{\alpha} + H_{D\alpha} + H_{T\alpha}) + H_C, \quad (1)$$

where $H_{\alpha} = \sum_{i \in \alpha} \varepsilon_i c_i^{\dagger} c_i$ is the Hamiltonian for the reservoirs, $H_{D\alpha} = \sum_{i \in D\alpha} \varepsilon_{Di} c_{Di}^{\dagger} c_{Di}$ for the dots, and $H_{T\alpha} = \sum_{i \in \alpha, j \in D\alpha} t_{ij} c_{Dj}^{\dagger} c_i + \text{h.c.}$ for tunneling between reservoirs and dots. H_C contains the Coulombic charging and interaction energies. We study a parameter regime where the charge states of the double dot can be truncated to the four lowest levels which we call $(0,0)$, $(1,0)$, $(0,1)$, and $(1,1)$. The ground state is labeled $(0,0)$ and (n_L, n_R) is the state with n_{α} excitations in dot α . The particles occupying the dots in the excited states can be either electrons or holes, and the Coulomb energy U is positive or negative depending on whether the two excitations in the $(1,1)$ state have equal or opposite charges. Sánchez and Büttiker³ use a similar energy level structure to produce a heat engine. However, their device requires energy filtering with single-level quantum dots, whereas our diode principle does not depend on the dot density of states and is therefore applicable also to metallic islands.

In the sequential tunneling approximation heat current is calculated in terms of the rates $\Gamma_{\alpha n}^{(\sigma)}$ for tunneling be-

tween reservoir α and the adjoining dot, with n being the occupation of the other dot and $\sigma = 1$ for tunneling into the dot, $\sigma = 0$ for tunneling into the reservoir. The probabilities $P_{n_L n_R}$ to be in state (n_L, n_R) are obtained from a steady-state master equation, and the heat current through the system, equal to the net energy extracted from the right reservoir, is then given by³

$$J = E_{R0}(P_{00}\Gamma_{R0}^{(1)} - P_{01}\Gamma_{R0}^{(0)}) + E_{R1}(P_{10}\Gamma_{R1}^{(1)} - P_{11}\Gamma_{R1}^{(0)}) \\ = U\tilde{\Gamma}^{-3}(\Gamma_{L0}^{(1)}\Gamma_{R1}^{(1)}\Gamma_{L1}^{(0)}\Gamma_{R0}^{(0)} - \Gamma_{R0}^{(1)}\Gamma_{L1}^{(1)}\Gamma_{R1}^{(0)}\Gamma_{L0}^{(0)}), \quad (2)$$

where the two terms on the second line correspond to the two cycles in Fig. 2(b), the normalization is $\tilde{\Gamma}^3 = \sum_{\alpha=L,R} \sum_{n,\sigma=0,1} \Gamma_{\alpha n}^{(\sigma)} \Gamma_{\alpha \bar{n}}^{(n)} (\Gamma_{\alpha \sigma}^{(\sigma)} + \Gamma_{\alpha \bar{\sigma}}^{(\bar{\sigma})})$, and a top bar denotes the other possible value, for example, $\bar{0} = 1$, $\bar{L} = R$. Fermi golden rule gives the tunneling rates as $\Gamma_{\alpha n}^{(\sigma)} = 2\pi\Gamma_{\alpha} F_{\alpha}((-1)^{\bar{\sigma}} E_{\alpha n})$, where $\Gamma_{\alpha} = \sum_{i \in \alpha} |t_i|^2 \delta(\varepsilon_i)$ is the tunneling strength for junction α , assumed to be energy independent. For metallic islands with a continuous spectrum the effective reservoir occupation is $F_{\alpha}(E) = E\nu_{D\alpha}n_{\alpha}(E)$, where $\nu_{D\alpha} = \sum_{i \in D\alpha} \delta(\varepsilon_{Di})$ is the island density of states and n_{α} is the Bose function. For quantum dots with a single discrete level $\varepsilon_{D\alpha}$ we have $F_{\alpha}(E) = f_{\alpha}(E)$, the Fermi function for reservoir α . Substituting these in Eq. (2) gives for a symmetric structure ($\Gamma_L = \Gamma_R \equiv \Gamma$)

$$J = A^{-1}U\Gamma[n_R(U) - n_L(U)]. \quad (3)$$

The diode effect is contained in the asymmetric weight function A , given for quantum dots as

$$A = \frac{2[1 + n_L(U)][1 + n_R(U)]}{f_{L0}(1 - f_{L1})f_{R0}(1 - f_{R1})} - 2 \quad (4)$$

and for metallic islands as

$$A = \nu_D^{-1} \sum_{\substack{\alpha=L,R \\ n,\sigma=0,1}} \frac{[\sigma + n_{\alpha}(U)][\bar{\sigma} + n_{\bar{\alpha}}(U)]}{E_{\alpha n}[\delta_{n\sigma} + n_{\alpha n}][\bar{n} - (-1)^n f_{\bar{\alpha}\delta_{n\sigma}}]}, \quad (5)$$

where $f_{\alpha n} = f_{\alpha}(E_{\alpha n})$, $n_{\alpha n} = n_{\alpha}(E_{\alpha n})$, and $\nu_D = \nu_{DL} = \nu_{DR}$.

The performance of the diode can be assessed by analyzing two key quantities, the heat current under forward bias, J_+ , and the ratio of forward and reverse currents, J_+/J_- . Forward bias is defined as the right reservoir having the high temperature T_H and the left reservoir having the low temperature T_C ; under reverse bias the temperatures are reversed. We start the analysis by making simplifications to Eqs. (3) and (4). First note that the constant term in Eq. (4) is practically always small compared to the total A and can be neglected. The four Fermi factors in the denominator of A are then divided into two groups: those with a value larger than $\frac{1}{2}$ are taken to be constants while the rest are approximated by exponentials. The device has two qualitatively different operating regimes, one with a positive and the other with a negative U , and we first consider $U > 0$. In this case

we have $1 - f_{\alpha 1} \approx 1$, giving the dependence of forward current on the energies $E_{\alpha 0}$ as $J_+ \propto e^{-\frac{E_{L0}}{T_C} - \frac{E_{R0}}{T_H}}$, and the rectification ratio as

$$J_+/J_- \approx e^{(T_C^{-1} - T_H^{-1})(E_{R0} - E_{L0})}. \quad (6)$$

We see that $(E_{R0} - E_{L0})/T_C$ should be large for efficient rectification while E_{L0}/T_C and E_{R0}/T_H should not be much above unity for a large forward current. Also, the difference in the temperatures should preferably be in the range $T_H/T_C \gtrsim 2$. Since by definition $(0,0)$ is the ground state, both energies $E_{\alpha 0}$ must be positive, and thus the optimal value of E_{L0} is zero. The energy E_{R0} can then be chosen to achieve the desired balance between forward current and diode efficiency. The interaction energy U has only a small effect on rectification but the forward current depends on it strongly. When $U \gg T_H$, the Bose functions in Eq. (3) suppress the current exponentially, while in the limit $U \ll T_H$ the Bose functions in Eq. (4) give a similar suppression. Thus the optimal value of U is of the order of T_H .

When considering the other operating regime, $U < 0$, we can restrict attention to the interval $E_{L0} < |U| < E_{R0}$ since a large $|U|$ would push the $(1,1)$ state below the ground state, while the above approximations for positive U are actually valid for $U > -E_{L0}$ and therefore the (uninteresting) case of $|U| < E_{L0}$ is contained in the previous discussion. Now we can approximate $1 - f_{R1} \approx 1$ while the three other Fermi factors in A are taken as exponentials. Then the current depends on the denominator of A as $J_+ \propto e^{-\frac{|U|}{T_C} - \frac{E_{R0}}{T_H}}$, and the rectification ratio is

$$J_+/J_- \approx e^{(T_C^{-1} - T_H^{-1})(E_{R0} - |U|)}. \quad (7)$$

Here $|U|$ has replaced E_{L0} in both expressions and therefore the device operation is almost independent of E_{L0} in this regime. Numerical calculations show that the forward current is maximized when $E_{L0} \approx 2T_C$.

Above we considered only the quantum dot setup, characterized by Eq. (4). However, the same approximations and conclusions can be derived from Eq. (5) by taking into account only the dominant two terms of the sum, that is, those terms where both occupation factors in the denominator are close to zero. The conclusions can also be verified by a numerical analysis of the full equations, as is done in Fig. 3. We see that both positive and negative U can produce similar levels of rectification but the forward current is larger for $U < 0$ and therefore we concentrate on that regime. To have an efficient diode with $J_+/J_- > 10$, we see that unless a temperature bias of $T_H/T_C > 3$ is available, the forward current cannot be larger than about $10^{-1} \Gamma_* T_C$, where $\Gamma_* = \Gamma$ for quantum dots and $\Gamma_* = \Gamma \nu_D E_{R0}$ for metal islands. On the other hand, if a current level of $10^{-2} \Gamma_* T_C$ is sufficient, considerable rectification takes place already for $T_H/T_C < 2$.

The validity of the above analysis requires that the dots are not coupled too strongly to the leads. Since

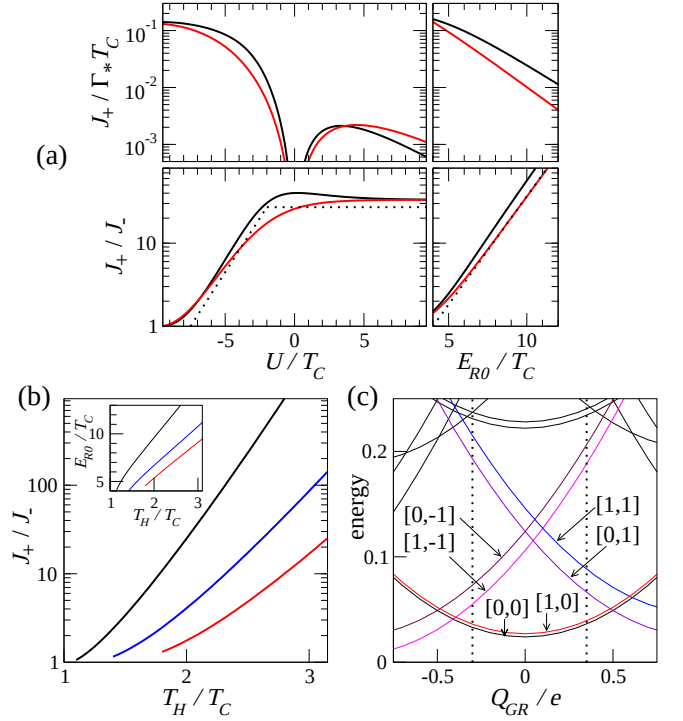


FIG. 3. (color online). (a) Forward current J_+ and the rectification ratio J_+/J_- as a function of U and E_{R0} . Black curves correspond to quantum dots ($\Gamma_* = \Gamma$), red for metal islands ($\Gamma_* = \Gamma \nu_D E_{R0}$). Dotted lines are the estimates from Eqs. (6) and (7). The parameters are $T_H = 2.5 T_C$, $E_{L0} = 2 T_C$, $E_{R0} = 7.5 T_C$ (left panels) and $U = -4 T_C$ (right panels). (b) Maximum rectification as a function of thermal bias T_H/T_C for fixed values of forward current. The three curves correspond to, from top to bottom, $J_+/\Gamma_* T_C = 0.01$ (black), 0.05 (blue), 0.1 (red). For each data point the parameters E_{L0} , E_{R0} and U are optimized to give maximum rectification for the given current. Optimal values of E_{R0} are shown in the inset, for E_{L0}/T_C they are in the range $2 \dots 3$, for U/T_C in the range $-5.5 \dots -3.5$. (c) Charging energies for the double dot as a function of the right gate charge Q_{GR} . The curves correspond to different charge states, with the relevant ones marked as $[N_L, N_R]$, where N_α is the number of electrons in dot α . Dotted lines highlight two values for Q_{GR} where the heat diode could be successfully operated, that is, the left and right transitions are well separated, and the lowest four levels are well separated from higher levels. Here the left gate charge is $Q_{GL} = .48 e$, the capacitance constants are $g_L = g_R = .1$, and the unit of energy is $e^2/(2C(1 - g_L g_R))$.

we require that only the lowest four levels are accessible, the tunneling rates should be smaller than the energies of the neglected higher-lying states. The energy scale for the forbidden transitions is set by E_{R0} and thus we must have $2\pi\Gamma_* \ll E_{R0}$. This coincides with the requirement that the junction conductances must be well below the conductance quantum. On the other hand, coupling strength must also be limited to prevent leakage currents due to cotunneling effects. As already discussed, the suppression of current under reverse bias is due to the fact that the low-energy particles are unable

to tunnel into the right dot. This blockade can be lifted by coherent two-electron processes where particles tunnel through both junctions simultaneously and most of the required energy is contributed by the left reservoir. There are two such cotunneling processes: if the system is initially in the $(0, 0)$ state, particles tunnel into both dots and the final state is $(1, 1)$; the other possible process leads from $(1, 0)$ to $(0, 1)$. In the supplementary material⁹ we present a detailed calculation of these processes and arrive at the conclusion that they can be neglected when Γ_* is bounded as above.

Let us now consider how to actually realize the required energy level structure in a double-dot setup. For a metallic island, the tunneling energy $E_{\alpha n}$ is simply the difference of electrostatic charging energies of the initial and final states, for the quantum dot system one must also add the bare energy of the discrete single-particle level, $\varepsilon_{D\alpha}$. Using the notation of Fig. 1(b), the charging energy for dots with charges Q_L and Q_R is

$$E_{ch}(Q_L, Q_R) = \frac{g_L(Q_L + Q_{GL})^2 + g_R(Q_R + Q_{GR})^2 + 2g_L g_R Q_L Q_R}{2C(1 - g_L g_R)} \quad (8)$$

with interaction constants $g_\alpha = C/(C + C_\alpha + G_{G\alpha})$ and gate charges $Q_{G\alpha} = C_{G\alpha}(V_{G\alpha} - V_\alpha) + g_{\bar{\alpha}}C_{\bar{\alpha}}(V_{\bar{\alpha}} - V_\alpha) + g_{\bar{\alpha}}C_{G\bar{\alpha}}(V_{G\bar{\alpha}} - V_\alpha)$. We see that the level structure is controlled by two gate charges which in turn depend on three voltages, and therefore in a practical implementation one of the voltages can be discarded. If in the ground state $(0, 0)$ the dots have charges Q_{L0} and Q_{R0} , then in the excited dots the charges are $Q_{L0} + q_L$ and $Q_{R0} + q_R$, where the q_α are $-e$ or $+e$ depending on whether the added excitation is an electron or a hole. From Eq. (8) we then see that the magnitude of U is determined by the capacitances as $|U| = e^2/[C(g_L^{-1}g_R^{-1} - 1)]$ while the energies E_{L0} and E_{R0} as well as the sign of U can be chosen with the gate charges. The energies $E_{\alpha 0}$ are

$$E_{L0} = E_{ch}(Q_{L0} + q_L, Q_{R0}) - E_{ch}(Q_{L0}, Q_{R0}) - \frac{q_L}{e}\varepsilon_{DL}$$

$$E_{R0} = E_{ch}(Q_{L0}, Q_{R0} + q_R) - E_{ch}(Q_{L0}, Q_{R0}) - \frac{q_R}{e}\varepsilon_{DR}$$

where the single-particle levels $\varepsilon_{D\alpha}$ vanish for metallic islands. If the truncation of the system to the four lowest charge states is to be valid, all higher states must have an energy much above all $E_{\alpha n}$. Of course the levels $E_{\alpha n}$ must themselves have the structure discussed above. Figure 3(c) shows two concrete examples of how to obtain appropriate level diagrams based on the above considerations.

Experimental demonstration of the diode effect must take place at around 1 K or below. First, the requirement of large absolute bias, $T_H/T_C \sim 2$, can only be attained at low temperatures. Second, since the device is based on Coulomb blockade physics, the charging energies attainable in mesoscopic structures set the maximum operating temperature to about 1 K. Third, in order to observe the thermal current through the diode, heat transport by phonons must be suppressed, and this generally takes place at sub-Kelvin temperatures.¹⁰ In a realistic setup we could have $T_C = 100$ mK, $T_H = 250$ mK, and $\Gamma_* = 0.5 T_C$, giving $\Gamma_* T_C \approx 10$ fW. Referring to Fig. 3, we see that it is then possible to have a forward current of the order of 1 fW with the reverse current being a few percent of this value. The forward current is large enough to be measured with state-of-the-art thermometry.¹¹

In summary, we propose a new device, a single-electron heat diode, which can be realized by a double-dot system connecting two electronic reservoirs at different temperatures. The device and required operation scheme are routinely realized with currently existing technology. We explored the rectification performance of the device in detail and showed that with experimentally measurable current levels it is possible to have a rectification ratio well above 10, even up to about 100, making the present device the first concrete proposal for an efficient heat diode.

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SUPPLEMENTARY MATERIAL: VIRTUAL TWO-PARTICLE TUNNELING RATES FOR THE SINGLE-ELECTRON HEAT DIODE

As explained in the main text, heat flow under reverse thermal bias is blocked because the golden-rule rates for hopping into the right dot are exponentially suppressed. This blockade can be lifted by coherent tunneling of electrons through both junctions simultaneously, with most of the energy contributed by the hot left reservoir. There are two different processes which can lift the blockade: if the system is initially in the $(0,0)$ state, particles can tunnel into both dots and the system ends up in the $(1,1)$ state. If, on the other hand, we start with the $(1,0)$ state, one particle hops out of the left dot and another one into the right dot, leaving the system in the $(0,1)$ state. Here we calculate the rates for these virtual transitions and show that in the parameter range relevant for diode operation they are negligible compared to sequential processes. The rates for two-particle transitions can be calculated from the general expression¹

$$\Gamma^{(2)} = 2\pi \sum_{f_b, i_a} |\langle f_b | H_T \frac{1}{E_{i_a} - H_0} H_T | i_a \rangle|^2 W_{i_a} \delta(E_{f_b} - E_{i_a}), \quad (1)$$

where $H_T = H_{TL} + H_{TR}$ is the tunneling Hamiltonian, $H_0 = H - H_T$ the uncoupled Hamiltonian, and W_{i_a} the probability weight for the initial states. For the process $(0,0) \rightarrow (1,1)$ the final state is related to the initial state by $|f_b\rangle = c_{DL}^\dagger c_L c_{DR}^\dagger c_R |i_a\rangle$. Note that this only applies to the case when the excitations for both dots are electrons. If, for instance, the excitation tunneling into the right dot is a hole, one should make the change $c_{DR}^\dagger c_R \rightarrow c_{DR} c_R^\dagger$. However, the formulas below will be identical in all the different cases. Writing the rate explicitly for metallic islands yields

$$\Gamma_{00 \rightarrow 11}^{(2)} = 2\pi \Gamma_L \Gamma_R \nu_{DL} \nu_{DR} \int d\varepsilon_L d\varepsilon_{DL} d\varepsilon_R d\varepsilon_{DR} f_L(\varepsilon_L) [1 - f_L(\varepsilon_{DL})] f_R(\varepsilon_R) [1 - f_R(\varepsilon_{DR})] \times \left| \frac{1}{\varepsilon_L - \varepsilon_{DL} - E_{L0} - \frac{i}{2}\Gamma_{10}} + \frac{1}{\varepsilon_R - \varepsilon_{DR} - E_{R0} - \frac{i}{2}\Gamma_{01}} \right|^2 \delta(\varepsilon_L + \varepsilon_R - \varepsilon_{DL} - \varepsilon_{DR} - E_{L0} - E_{R0} - U). \quad (2)$$

The two energy denominators correspond to the two different orderings in which the electron hoppings can occur. To regularize the divergences of the denominators we have introduced the inverse lifetimes $\Gamma_{n_L n_R}^{(0)}$ of the state (n_L, n_R) , calculated with the lowest-order golden rule. Thus we have, for example, $\Gamma_{10} = \Gamma_{L0}^{(0)} + \Gamma_{R1}^{(1)}$. In the case of quantum dots the corresponding rate is

$$\Gamma_{00 \rightarrow 11}^{(2)} = 2\pi \Gamma_L \Gamma_R \int d\varepsilon_L d\varepsilon_R f_L(\varepsilon_L) f_R(\varepsilon_R) \left| \frac{1}{\varepsilon_L - E_{L0} - \frac{i}{2}\Gamma_{10}} + \frac{1}{\varepsilon_R - E_{R0} - \frac{i}{2}\Gamma_{01}} \right|^2 \delta(\varepsilon_L + \varepsilon_R - E_{L0} - E_{R0} - U). \quad (3)$$

For the other relevant cotunneling process, from $(1,0)$ to $(0,1)$, the metallic system has

$$\Gamma_{10 \rightarrow 01}^{(2)} = 2\pi \Gamma_L \Gamma_R \nu_{DL} \nu_{DR} \int d\varepsilon_L d\varepsilon_{DL} d\varepsilon_R d\varepsilon_{DR} [1 - f_L(\varepsilon_L)] f_L(\varepsilon_{DL}) f_R(\varepsilon_R) [1 - f_R(\varepsilon_{DR})] \times \left| \frac{1}{\varepsilon_{DL} - \varepsilon_L - E_{L0} - \frac{i}{2}\Gamma_{00}} + \frac{1}{\varepsilon_R - \varepsilon_{DR} - E_{R1} - \frac{i}{2}\Gamma_{11}} \right|^2 \delta(-\varepsilon_L + \varepsilon_R + \varepsilon_{DL} - \varepsilon_{DR} + E_{L0} - E_{R0}), \quad (4)$$

and analogously for the quantum dot setup.

Equations (2) and (4) suggest that for the metallic system it is useful to define new integration variables $\varepsilon'_\alpha = \varepsilon_\alpha - \varepsilon_{D\alpha}$. Then with the help of the identities $f_\alpha(\varepsilon'_\alpha + \varepsilon_{D\alpha})[1 - f_\alpha(\varepsilon_{D\alpha})] = n_\alpha(\varepsilon_{D\alpha})[f_\alpha(\varepsilon_{D\alpha}) - f_\alpha(\varepsilon'_\alpha + \varepsilon_{D\alpha})]$ and $\int d\varepsilon_{D\alpha} [f_\alpha(\varepsilon_{D\alpha}) - f_\alpha(\varepsilon'_\alpha + \varepsilon_{D\alpha})] = \varepsilon'_\alpha$ the variables $\varepsilon_{D\alpha}$ can be integrated out. For both metallic and quantum dot cases the delta function can be used to eliminate another of the remaining integration variables, and then all the tunneling rates can be expressed with a single equation:

$$\Gamma_\Delta^{(2)} = 2\pi \Gamma_L \Gamma_R U^2 \int d\varepsilon F_L(\Delta - \varepsilon) F_R(\varepsilon) \left| \frac{1}{\varepsilon - E_{R0} - \frac{i}{2}\Gamma_0} \right|^2 \left| \frac{1}{\varepsilon - E_{R1} - \frac{i}{2}\Gamma_1} \right|^2, \quad (5)$$

where $F_\alpha(\varepsilon) = f_\alpha(\varepsilon)$ for quantum dots and $F_\alpha(\varepsilon) = \varepsilon \nu_{D\alpha} n_\alpha(\varepsilon)$ for a metallic system. For the $(0,0) \rightarrow (1,1)$ transition the parameters are $\Delta = E_{L0} + E_{R0} + U$, $\Gamma_0 = \Gamma_{01}$, and $\Gamma_1 = \Gamma_{10}$, and for the $(1,0) \rightarrow (0,1)$ transition they are $\Delta = E_{R0} - E_{L0}$, $\Gamma_0 = \Gamma_{00}$, and $\Gamma_1 = \Gamma_{11}$.

It is important to notice that Eq. (5) gives the total transition rates, including both sequential tunneling and cotunneling.² Sequential contribution comes from the resonance peaks at $\varepsilon = E_{R0}$ and $\varepsilon = E_{R1}$, while the rest, due to the peak in the function $F_L(\Delta - \varepsilon)F_R(\varepsilon)$, is the cotunneling contribution. The sequential rate can therefore be calculated by taking the limit $|\varepsilon - E - \frac{i}{2}\Gamma|^{-2} \rightarrow \frac{2\pi}{\Gamma}\delta(\varepsilon - E)$. We get

$$\Gamma_{00 \rightarrow 11, \text{seq}}^{(2)} = \frac{\Gamma_{R0}^{(1)}\Gamma_{L1}^{(1)}}{\Gamma_{01}} + \frac{\Gamma_{L0}^{(1)}\Gamma_{R1}^{(1)}}{\Gamma_{10}}; \quad \Gamma_{10 \rightarrow 01, \text{seq}}^{(2)} = \frac{\Gamma_{R1}^{(1)}\Gamma_{L1}^{(0)}}{\Gamma_{11}} + \frac{\Gamma_{L0}^{(0)}\Gamma_{R0}^{(1)}}{\Gamma_{00}}. \quad (6)$$

This is exactly the result one would expect; for example, the first term in the $(0,0) \rightarrow (1,1)$ process is the rate of the $(0,0) \rightarrow (0,1)$ transition, multiplied by the probability that the next transition leads to $(1,1)$. The second term similarly gives the rate for the process $(0,0) \rightarrow (1,0) \rightarrow (1,1)$.

To calculate the cotunneling rate we note that for $\exp(\Delta/T_H) \gg 1$ we can approximate $F_L(\Delta - \varepsilon)F_R(\varepsilon) \approx e^{-\Delta/T_H}(e^{\varepsilon(T_C^{-1}-T_H^{-1})} + e^{-\varepsilon/T_H})^{-1}$ for the quantum dot system. This function has a peak at $|\varepsilon| \lesssim T_C$ and it decays exponentially with $1/(T_C^{-1} - T_H^{-1})$ and T_H for positive and negative ε , respectively. In this region we can approximate $E_{Rn} - \varepsilon \approx E_{Rn}$ and therefore the cotunneling contribution can be extracted by setting $|\varepsilon - E - \frac{i}{2}\Gamma|^{-2} \rightarrow E^{-2}$ in Eq. (5). The result is

$$\Gamma_{\Delta, \text{cot}}^{(2)} = \frac{2\pi^2 \Gamma_L \Gamma_R U^2 T_C}{E_{R0}^2 E_{R1}^2 \sin \pi \frac{T_C}{T_H}} e^{-\Delta/T_H} \quad (7)$$

for quantum dots. Similar considerations apply also in the metallic case, and the cotunneling rate is

$$\Gamma_{\Delta, \text{cot}}^{(2)} = \frac{2\pi^3 \Gamma_L \Gamma_R \nu_{DL} \nu_{DR} U^2 T_C^2 \Delta}{E_{R0}^2 E_{R1}^2 \sin^2 \pi \frac{T_C}{T_H}} e^{-\Delta/T_H}. \quad (8)$$

The relevance of cotunneling can now be estimated by comparing the magnitudes of $\Gamma_{\text{cot}}^{(2)}$ and $\Gamma_{\text{seq}}^{(2)}$. For a symmetric system, $\Gamma_L = \Gamma_R \equiv \Gamma$, with $U \gtrsim T_H$, we have

$$\frac{\Gamma_{\text{cot}}^{(2)}}{\Gamma_{\text{seq}}^{(2)}} \approx \frac{\pi \Gamma_{\text{eff}} U^2 T_C}{E_{R0}^2 E_{R1}^2} e^{E_{L0}/T_H} e^{E_{R0}(T_C^{-1} - T_H^{-1})}, \quad (9)$$

where $\Gamma_{\text{eff}} = \Gamma$ for quantum dots and $\Gamma_{\text{eff}} = \pi \Gamma \nu_D T_C$ for metal islands. We have used the rates for the $(1,0) \rightarrow (0,1)$ transition since the ratio would be smaller for the $(0,0) \rightarrow (1,1)$ transition. For $U \lesssim -T_H$ the latter process dominates and we have

$$\frac{\Gamma_{\text{cot}}^{(2)}}{\Gamma_{\text{seq}}^{(2)}} \approx \frac{\pi \Gamma_{\text{eff}} U^2 T_C}{E_{R0}^2 E_{R1}^2} e^{-E_{L0}/T_H} e^{E_{R1}(T_C^{-1} - T_H^{-1})}. \quad (10)$$

For the parameter values corresponding to the plots in Fig. 3 of the main text, with $\Gamma_{\text{eff}} < T_C$, these ratios are smaller than 10%, and therefore we conclude that cotunneling effects are negligible for the proposed device.

¹ H. Bruus and K. Flensberg, *Many-Body Quantum Theory in Condensed Matter Physics* (Oxford University Press, Oxford, 2004).

² Yu. V. Nazarov and Ya. M. Blanter, *Quantum Transport* (Cambridge University Press, Cambridge, 2009).